

## Tutorial Day Presenters

**James A. Cooper** is professor of Electrical and Computer Engineering at Purdue University. His group is responsible for a number of advances in SiC technology, including the first DMOS power transistor (1996), the oxide-protected UMOS power transistor (1998), the self-aligned short-channel DMOSFET (2003), and the first n-channel IGBT on a free-standing epilayer (2010). Prof. Cooper is a Life Fellow of the IEEE, and has co-authored over 250 journal articles and conference presentations, 18 US patents, and the textbook *Fundamentals of Silicon Carbide Technology* (John Wiley, 2014).

**Tsunenobu Kimoto** received the M.E. degrees in Electrical Engineering from Kyoto University, Japan, in 1988. After working at Sumitomo Electric Industries, he started his academic career at Kyoto University in 1990, and received the Ph.D. degree in 1996 based on his work on SiC. From 1996 to 1997, he was a visiting scientist at Linköping University, Sweden. He is currently a Professor of Kyoto University. His main research activity includes SiC growth, characterization, defect electronics, processing, and high-voltage devices. He is a member of IEEE (Fellow), JSAP (Fellow), MRS, IEICE, and IEE.

**Victor Veliadis** received the five year diploma degree from the National Technical University of Athens Greece in 1990, and the Masters and Ph.D. degrees from Johns Hopkins University in 1992 and 1995, respectively, all in Electrical and Computer Engineering. From 1996 to 2000, he was with Nanocrystals Imaging Corporation where he developed quantum-dot phosphors for imaging applications. From 2000 to 2003, he was with Lucent Technologies where he designed InP-based tunable photonic integrated circuits for telecommunication applications. In 2003, Victor was Adjunct Physics Professor at Ursinus College and St. Joseph's University. After a brief military service, Victor joined Northrop Grumman Electronic Systems in 2004 where he designed, fabricated, and tested SiC JFETs, MOSFETs, Thyristors, and JBS, Schottky, and PiN diodes in the 1-12 kV range. In May 2016 Victor was appointed CTO of Power America, which is a U.S. Department of Energy Manufacturing Institute managed by North Carolina State University (NCSU). At that time Victor also became Professor in Electrical and Computer Engineering at NCSU. Dr. Veliadis has authored 105 peer-reviewed technical articles, 3 book chapters, and has 23 issued patents to his credit.

**Sima Dimitrijević** received the B.Eng., M.Sci., and Ph.D. degrees in electronic engineering from the University of Nis, Nis, Yugoslavia, in 1982, 1985, and 1989, respectively. From 1982 to 1983, he was with the Semiconductor Factory of the Electronics Industry, Nis, where he worked on the development of CMOS technology. From 1983 to 1990, he was with the Faculty of Electronic Engineering, University of Nis. In 1990, he joined Griffith University, Brisbane, Australia, where he is currently a Professor at the Griffith School of

Engineering and the Deputy Director of Queensland Micro- and Nanotechnology Centre. His current research interests are focused on semiconductor devices for post-silicon power electronics and demonstration of a know-how model for research commercialization. He is the author of Principles of Semiconductor Devices, 2nd Ed. (New York: Oxford University Press, 2011) and a member of the Editorial Board of Microelectronics Reliability.

**Alberto Castellazzi** is Associate Professor of Power Electronics at the University of Nottingham, Nottingham, UK. His research interests are characterization, modelling, application, packaging and thermal management of power devices. He has been active in power electronics research and development for over 15 years and has had extensive collaborations with major European and international industrial research laboratories and groups on publicly and privately funded research projects. He has authored and co-authored over 140 papers in peer reviewed specialist journals and conferences, for which he also regularly acts as a reviewer. Dr. Castellazzi is a member of the Technical Programme Committee of the ISPSD, ESTC, ESREF and PEMD conferences.

**Rahul Chokhawala** is a Power Semiconductor Specialist with GE Global Research. He is the holder of a M.Sc. in Control Systems from the University of Iowa, Iowa City, USA, and of a M.Tech. in Power Electronics from the Indian Institute of Technology, Chennai, India. He has held former positions with International Rectifier, Motorola, ABB Semiconductor, ABB Process Automation, and American Superconductor. Rahul Chokhawala is the holder of a number of patents and IEEE publications in the area of power semiconductor protection and applications.

**Scott Allen** is the Manager of Power Research and Development at Wolfspeed. Dr. Allen has been with Wolfspeed/Cree for 22 years and has been involved in many aspects of wide bandgap device development for both power and RF applications. In his current role, he is responsible for the team of scientists and engineers that are maturing the next generation of SiC power technology for product readiness and for developing future products with extremely high voltage ratings. His prior responsibilities include both Operations and Power Marketing, and he is now applying what he learned from the customer community to match the next generation of products to industry need. He performed his undergraduate studies at Cornell University and received his Ph.D. from U.C. Santa Barbara.